



## This technology is currently not available for licensing

Tech ID: 19158

### ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- ▶ Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- ▶ Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- ▶ Methods to Produce and Recycle Substates for III-Nitride Materials with Electrochemical Etching
- ▶ A Structure For Increasing Mobility In A High-Electron-Mobility Transistor
- ▶ III-Nitride Tunnel Junction with Modified Interface
- ▶ Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- ▶ (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- ▶ Thermally Stable, Laser-Driven White Lighting Device
- ▶ GaN-based Vertical Metal Oxide Semiconductor and Junction Field Effect Transistors
- ▶ III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- ▶ Iii-N Transistor With Stepped Cap Layers
- ▶ A Method To Lift-Off Nitride Materials With Electrochemical Etch
- ▶ Activation of P-Type Layers of Tunnel Junctions in Micro-LEDs
- ▶ High-Intensity Solid State White Laser Diode
- ▶ Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- ▶ Epitaxial Light Control Features in Light Emitting Diodes
- ▶ High-Efficiency Vertical Cavity Surface Emitting Laser Fabrication
- ▶ A Wafer-Scale, Low Defect Density Strain Relaxed Template for III-Nitride-Based High Efficiency and High-Power Devices
- ▶ III-N Based Material Structures and Circuit Modules Based on Strain Management

